

3V GENERAL PURPOSE AMPLIFIER

RF2323

Typical Applications

- Broadband Gain Blocks
- Low Noise Amplifiers
- IF or RF Buffer Amplifiers

- Driver Stage for Power Amplifiers
- Oscillator Loop Amplifiers
- Receiver Front-Ends

Product Description

The RF2323 is a general purpose, low-cost silicon amplifier designed for operation from a 3V supply. The circuit configuration with resistive feedback allows for broadband cascadable amplification. Capacitive compensation extends the bandwidth of the amplifier and input stage design optimizes noise figure. The device is unconditionally stable and internally matched to 50Ω . The only external components required for specified performance are bypass and DC blocking capacitors (as shown in application schematic). The RF2323 is available in a very small industry-standard SOT-23 5-lead surface mount package, enabling compact designs which conserve board space.





Functional Block Diagram



Package Style: SOT 5-Lead

Features

- DC to >2000MHz Operation
- 2.7 V to 3.3 V Single Supply
- 2.3dB Noise Figure
- 21 dB Gain at 900 MHz
- 12dB Gain at 1900MHz
- High Isolation (33dB at 900MHz)



Absolute Maximum Ratings

Parameter	Rating	Unit
Supply Voltage	4.0	V
Operating Ambient Temperature	-40 to +85	°C
Storage Temperature	-40 to +150	°C



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Parameter	Specification		Unit	Condition		
Faialletei	Min.	Тур.	Max.	Onit		
Overall					T=27 °C, V _{CC} =3.0V	
Frequency Range		DC to >2000		MHz		
100MHz Performance					T=27 °C, V _{CC} =3.0V	
Gain		20		dB		
Noise Figure		2.0		dB		
Output IP3		5		dBm		
Output P _{1dB}		-6		dBm		
Input Return Loss		19		dB		
Output Return Loss		12		dB		
Isolation		50		dB		
500MHz Performance					T=27 °C, V _{CC} =3.0V	
Gain		19		dB		
Noise Figure		2.3		dB		
Output IP3		4		dBm		
Output P _{1dB}		-6		dBm		
Input Return Loss		9		dB		
Output Return Loss		11		dB		
Isolation		41		dB		
900MHz Performance					T=27 °C, V _{CC} =3.0V	
Gain	19.0	21	21.5	dB		
Noise Figure		2.3		dB		
Output IP3		2		dBm		
Output P _{1dB}		-7		dBm		
Input Return Loss		6		dB		
Output Return Loss		8		dB		
Isolation		33		dB		
1000 MHz Performance					T=27 °C, V _{CC} =3.0V	
Gain		20		dB		
Noise Figure		2.3		dB		
Output IP3		2		dBm		
Output P _{1dB}		-7		dBm		
Input Return Loss		6		dB		
Output Return Loss		8		dB		
Isolation		32		dB		
2000 MHz Performance					T=27 °C, V _{CC} =3.0V	
Gain		12		dB		
Noise Figure		4.0		dB		
Output IP3		3		dBm		
Output P _{1dB}		-7		dBm		
Input Return Loss		14		dB		
Output Return Loss		20		dB		
Isolation		27		dB		
Power Supply						
Operating Voltage		3.0±10%		V		
Operating Current		6.8		mA	V _{CC} =3.0V	

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Pin	Function	Description	Interface Schematic
1	GND	Ground connection. Keep traces physically short and connect immedi- ately to ground plane for best performance.	
2	GND	Same as pin 1.	
3	RF IN	RF input pin. This pin is not internally DC blocked and thus requires an external blocking capacitor suitable for the frequency of operation. The input impedance of this pin is internally matched to 50Ω using resistive feedback.	
4	VCC	Supply connection. This pin should be bypassed with a suitable capac- itor(s).	-
5	RF OUT	RF output and bias pin. The output impedance of this pin is internally matched to 50Ω using resistive feedback. Because DC biasing is present on this pin, a DC blocking capacitor should be used in most applications (see application schematic).	See pin 3 schematic.

Application Schematic



Evaluation Board Schematic (Download <u>Bill of Materials</u> from www.rfmd.com.)



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Evaluation Board Layout 1" x 1"







RF2323

Preliminary



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Rev A4 010720



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